

Amendments to the Specification are as follows:

Please amend the paragraph on page 65, lines 2-8 as follows:

Since the outer layers 68 and 71 in contact with the nonmagnetic conductive layers 42-43 and 48, respectively, are formed of Co, the rate of change of resistance can be increased and mutual diffusion between the inner component 70 and the nonmagnetic conductive layer 48 and between the inner layers 69 and the nonmagnetic conductive layer 43 can be prevented.

Please amend the paragraph on page 69, lines 8-21 as follows:

The spin-valve thin-film magnetic element 2 of the second embodiment has the same advantages as that of the spin-valve thin-film magnetic element 1 of the first embodiment. In addition, the magnetization vectors of the first and second free magnetic sublayers layers-67 and 65, respectively, are antiparallel to each other by an exchange anisotropic magnetic field (a RKKY interaction) generated between the first and second free magnetic sublayers layers-67 and 65, respectively. The magnetization vectors of the first and second free magnetic sublayers 67 and 65, respectively, are reversible while maintaining ferrimagnetism by the effect of an external magnetic field. As a result, the spin-valve thin-film magnetic element 2 has a greater rate of change of resistance.

Please amend the abstract as follows:

A spin-valve thin-film magnetic element includes biasing and conductive layers and a substrate, a laminate formed on the substrate, biasing layers, and conductive layers. The laminate that includes a free magnetic layer; a first nonmagnetic conductive layer; a first pinned magnetic layer and a first antiferromagnetic layer deposited on the upper surface, away from the substrate, of the free magnetic layer; a second nonmagnetic conductive layer; a second pinned magnetic layer and a second antiferromagnetic layer deposited on the lower surface, near the substrate, of the free magnetic layer. The biasing layers orient the magnetization vector of the free magnetic layer in a direction perpendicular to the magnetization vector that of the pinned magnetic layers, and the conductive layers supply a sensing current to the free magnetic layer. The magnetization vectors of the first and second pinned magnetic layers are fixed in antiparallel directions by the first and second antiferromagnetic layers respectively adjoining the first pinned magnetic layer fixes the magnetization vector of the first pinned magnetic layer in one direction. The second antiferromagnetic layer adjoining the second pinned magnetic layer fixes the magnetization vector of the second pinned magnetic layer in a direction antiparallel to the magnetization

vector of the first pinned magnetic layer. In addition, ~~t~~The first and second antiferromagnetic layers are composed of an alloy comprising contain Mn and at least one element selected from the group consisting of Pt, Pd, Ir, Rh, Ru, Os, Au, Ag, Cr, Ni, Ne, Ar, Xe and/or Kr.